

Vishay Semiconductors

Phase Control Thyristor RMS SCRs, 25 A, 35 A



TO-48 (TO-208AA)

PRIMARY CHARACTERISTICS						
I _{T(AV)}	16 A, 22 A					
I _{T(RMS)}	25 A, 35 A					
V _{DRM} /V _{RRM}	25 V, 50 V, 100 V, 150 V, 200 V, 250 V, 300 V, 400 V, 500 V, 600 V, 700 V, 800 V, 1000 V 1200 V					
V _{TM}	2.3 V					
I _{GT}	60 mA					
T_J	-40 °C to +125 °C					
Package	TO-48 (TO-208AA)					
Circuit configuration	Single SCR					

FEATURES

- · General purpose stud mounted
- Broad forward and reverse voltage range through 1200 V



 Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES 2N681-92	VALUES 2N5205-07	UNITS		
1		16 ⁽¹⁾	22 (1)	А		
I _{T(AV)}	T _C	-65 to +65 ⁽¹⁾	-40 to +40	°C		
I _{T(RMS)}		25	35	А		
1	50 Hz	145	285	А		
I _{TSM}	60 Hz	150 ⁽¹⁾	300 (1)			
2t	50 Hz	103	410	A ² s		
1-1	60 Hz	94	375			
I _{GT}		40	40	mA		
dV/dt		=	100 (1)	V/µs		
dl/dt		75 to 100	100	A/µs		
V_{DRM}	Range	25 to 800	600 to 1200	V		
V _{RRM}	Range	25 to 800	600 to 1200	V		
T _J		-65 to +125 ⁽¹⁾	-40 to +125 ⁽¹⁾	°C		

Note

(1) JEDEC® registered value



Vishay Semiconductors

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS (APPLIED GATE VOLTAGE ZERO OR NEGATIVE)						
TYPE NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK REVERSE AND OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE ($t_p < 5 \text{ ms}$)	TJ			
VS-2N681	25	35				
VS-2N682	50	75				
VS-2N683	100	150				
VS-2N684	150	200				
VS-2N685	200	300				
VS-2N686	250	350	65 °C to 1105 °C			
VS-2N687	300	400	-65 °C to +125 °C			
VS-2N688	400	500				
VS-2N689	500	600				
VS-2N690	600	720				
VS-2N691	700	840				
VS-2N692	800	960				
VS-2N5205	800	960				
VS-2N5206	1000	1200	-40 °C to +125 °C			
VS-2N5207	1200	1440				

Note

• JEDEC registered values

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CON	VALUES 2N681-92	VALUES 2N5205-07	UNITS			
Maximum average on-state	I _{T(AV)}	180° half sine wave condu	ction	16 ⁽¹⁾	22 ⁽¹⁾	Α		
current at case temperature	TI(AV)	100 Hall Sille wave collud	Ction	-65 to +65 ⁽¹⁾	-40 to +40 ⁽¹⁾	°C		
Maximum RMS on-state current	I _{T(RMS)}			25	35	Α		
		50 Hz half cycle sine wave or 6 ms rectangular pulse	Following any rated load condition, and with rated V _{RRM} applied following surge Same conditions as above except with V _{RRM} applied following surge = 0	145	285			
Maximum peak, one-cycle	I _{TSM}	60 Hz half cycle sine wave or 5 ms rectangular pulse		150 ⁽¹⁾	300 (1)	Α		
non-repetitive surge current		50 Hz half cycle sine wave or 6 ms rectangular pulse		170	340			
		60 Hz half cycle sine wave or 5 ms rectangular pulse		180	355			
		t = 10 ms	Rated V _{RRM} applied	103	410			
Maximum I ² t capability for fusing	I ² t	t = 8.3 ms	following surge, initial T _J = 125 °C	94	375	A ² s		
Maximum I ² t capability for		t = 10 ms	V _{RRM} = 0 following	145	580			
individual device fusing		t = 8.3 ms	surge, initial $T_J = 125 ^{\circ}\text{C}$	135	530			
Maximum l ² √t capability for individual device fusing	I ² √t (2)	$t = 0.1$ ms to 10 ms, initial V_{RRM} applied following sur	1450	5800	A²√s			
Maximum peak on-state voltage	V_{TM}	$T_J = 25$ °C, $I_{T(AV)} = 16$ A (50 $I_{T(AV)} = 22$ A (70 A peak) 2N	2 (1)	2.3 (1)	V			
Maximum holding current	I _H	Anode supply 24 V, initial I	20 at 25 °C (typical)	200 ⁽¹⁾ at -40 °C	mA			

Notes

⁽¹⁾ JEDEC registered value

⁽²⁾ I^2t for time $t_x = I^2 \sqrt{t} \cdot \sqrt{t_x}$



Vishay Semiconductors

SWITCHING							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES 2N681-92	VALUES 2N5205-07	UNITS	
	V _{DM} = 25 V to 600 V		$T_C = 125 ^{\circ}\text{C}, V_{DM} = \text{Rated } V_{DRM},$	100	-		
Maximum non-repetitive	V _{DM} = 700 V to 800 V	dl/dt	I_{TM} = 2 x dl/dt, gate pulse = 20 V, 15 Ω, t_p = 6 μs, t_r = 0.1 μs maximum Per JEDEC standard RS-397, 5.2.2.6	75	-	A/µs	
rate of rise of turned-on current		ui/at	T_C = 125 °C, V_{DM} = 600 V, I_{TM} = 200 A at 400 Hz maximum, gate pulse = 20 V, 15 Ω , t_p = 6 μ s, t_r = 0.1 μ s maximum Per JEDEC standard RS-397, 5.2.2.6	-	100	Ανμδ	
Typical delay time		t _d	T_C = 25 °C, V_{DM} = Rated V_{DRM} , I_{TM} = 10 A DC resistive circuit, gate pulse = 10 V, 40 Ω source, t_p = 6 μ s, t_r = 0.1 μ s	1	1	μs	

BLOCKING								
PARAMETER		SYMBOL	TEST CONDITIONS		VALUES 2N681-92	VALUES 2N5205-07	UNITS	
Minimum critical rate	of	d)//dt	$T_J = 125$ °C, exponential to 100 % rated V_{DRM}	Gate open	100 (typical)	100 (1)	\//a	
rise of off-state voltage		dV/dt	$T_J = 125$ °C, exponential to 67 % rated V_{DRM}	circuited	250 (typical)	250	V/µs	
	V_{RRM} , $V_{DRM} = 400 \text{ V}$		·		3.5	-		
	V_{RRM} , $V_{DRM} = 500 V$		T _J = 125 °C		3.5	ı		
Marrian	V_{RRM} , $V_{DRM} = 600 V$] ,			2.5	3.3		
Maximum reverse leakage current	V_{RRM} , $V_{DRM} = 700 V$	I _{DRM} ,			2.2	-	mA	
	V_{RRM} , $V_{DRM} = 800 V$	IRRM			2	2.5		
	V _{RRM} , V _{DRM} = 1000 V				-	2		
V_{RRM} , $V_{DRM} = 1200 \text{ V}$					_	1.7		

Note

(1) JEDEC registered value

TRIGGERING						
PARAMETER	SYMBOL		TEST CONDITIONS		VALUES 2N5205-07	UNITS
Maximum peak gate power	P _{GM}		t _p < 5 ms for 2N681 series; t _p < 500 μs for 2N5204 series		60 ⁽¹⁾	W
Maximum average gate power	P _{G(AV)}			0.5 (1)	0.5 (1)	
Maximum peak positive gate current	+I _{GM}			2 (1)	2	Α
Maximum peak positive gate voltage	+V _{GM}			10 ⁽¹⁾	-	V
Maximum peak negative gate voltage	-V _{GM}			5 ⁽¹⁾	5 ⁽¹⁾	V
Maximum required DC gate		T _C = min. rated value	Maximum required gate trigger current is the lowest value which will trigger all units with + 6 V anode to cathode	80 (1)	80 (1)	
current to trigger	I _{GT}	T _C = 25 °C		40	40	mA
		T _C = 125 °C		18.5	20	
Typical DC gate current to trigger		$T_C = 25 ^{\circ}C, +$	6 V anode to cathode	30	30	
Maximum required DC gate voltage to trigger	V _{GT}	T _C = -65 °C	Maximum required gate trigger voltage is the lowest value which will trigger all units with + 6 V anode to cathode	3 (1)	3 (1)	V
		T _C = 25 °C		2	2	
Typical DC gate voltage to trigger		T _C = 25 °C, + 6 V anode to cathode		1.5	1.5	
Maximum DC gate voltage not to trigger	V_{GD}	T _C = 125 °C	Maximum gate voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode	0.25 (1)	0.25 (1)	V

Note

(1) JEDEC registered value



Vishay Semiconductors

THERMAL AND MECHANICAL SPECIFICATIONS								
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES 2N681-92	VALUES 2N5205-07	UNITS		
Operating junction and storage temperature range		T _J , T _{Stg}		-65 to 125 ⁽¹⁾	-40 to 125 ⁽¹⁾	°C		
Maximum internal thermal resistance, junction to case		R _{thJC}	DC operation	1.5	1.5 ⁽¹⁾	°C/W		
Typical thermal resistance, case to sink		R _{thCS}	Mounting surface, smooth, flat and greased	0.35	0.35	C/VV		
			Lukii atad thusada	20 (27.5)		lbf ⋅ in		
	to nut		Lubricated threads (Non-lubricated threads)	0.23 (0.32)		kgf · cm		
Mounting torque		(NON-Tublicated tilleads)		2.3 (3.1)		N·m		
± 10 %	± 10 % to device		Lubricated threads		25			
					0.29			
				2.8		N·m		
Approximate weight	Approximate weight			14	14	g		
Approximate weight				0.49	0.5	OZ.		
Case style				TO-48 (TO-208AA)		·		

Note

⁽¹⁾ JEDEC registered value

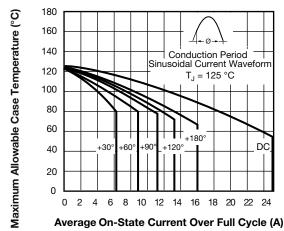


Fig. 1 - Maximum Allowable Case Temperature vs. Average On-State Current, 2N681 Series

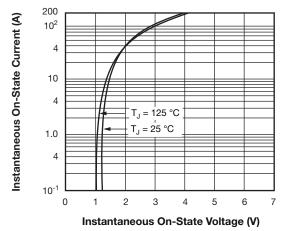
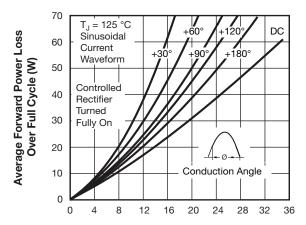


Fig. 2 - Maximum On-State Voltage vs. Current, 2N681 Series

Vishay Semiconductors



Average On-State Current Over Full Cycle (A)

Fig. 3 - Maximum Low Level On-State Power Loss vs. Current (Sinusoidal Current Waveform), 2N681 Series

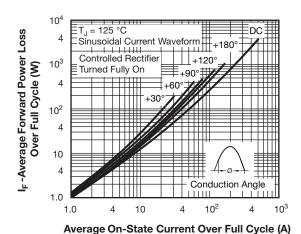
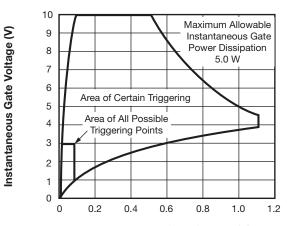


Fig. 4 - Maximum High Level On-State Power Loss vs. Current (Sinusoidal Current Waveform), 2N681 Series



Instantaneous Gate Current (A)
Fig. 5 - Gate Characteristics,
2N681 Series

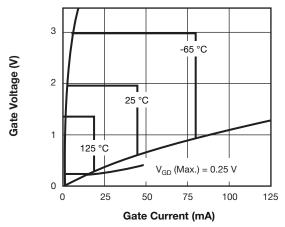


Fig. 5a - Area of All Possible Triggering Points vs. Temperature, 2N681 Series

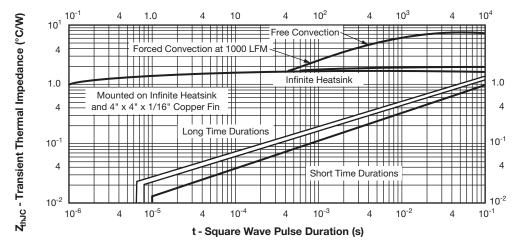


Fig. 6 - Maximum Transient Thermal Impedance, Junction to Case, vs. Pulse Duration, 2N681 Series

Vishay Semiconductors

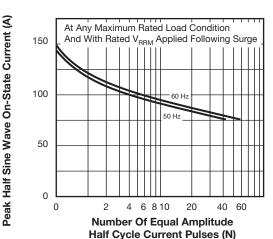


Fig. 7 - Maximum Non-Repetitive Surge Current vs. Number of Current Pulses, 2N681 Series

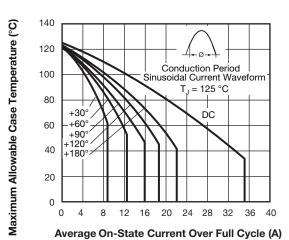


Fig. 8 - Maximum Allowable Case Temperature vs. Average On-State Current (Sinusoidal Current Waveform), 2N5205 Series

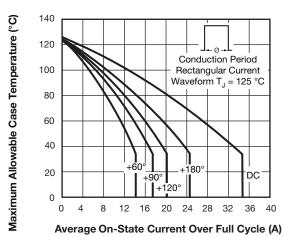
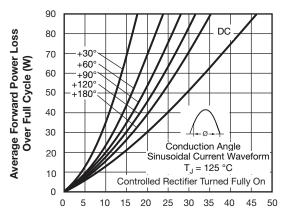


Fig. 9 - Maximum Allowable Case Temperature vs. Average On-State Current (Rectangular Current Waveform), 2N5205 Series



Average On-State Current Over Full Cycle (A)

Fig. 10 - Maximum Low-Level On-State Power Loss vs. Average On-State Current (Sinusoidal Current Waveform), 2N5205 Series

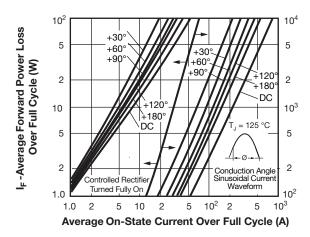
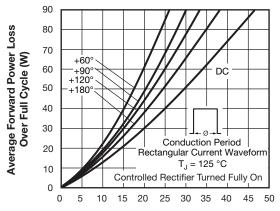


Fig. 11 - Maximum High-Level On-State Power Loss vs. Average On-State Current (Sinusoidal Current Waveform), 2N5205 Series



Average On-State Current Over Full Cycle (A)

Fig. 12 - Maximum Low-Level On-State Power Loss vs. Average On-State Current (Rectangular Current Waveform), 2N5205 Series



Vishay Semiconductors

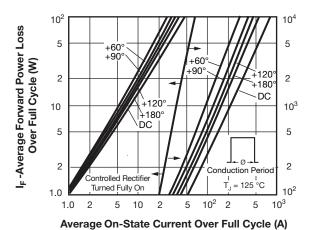


Fig. 13 - Maximum High-Level On-State Power Loss vs. Average On-State Current (Rectangular Current Waveform), 2N5205 Series

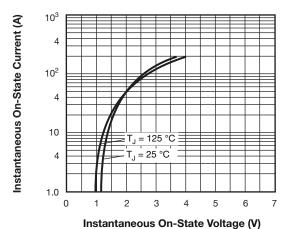


Fig. 14 - Maximum Instantaneous On-State Voltage vs. Instantaneous On-State Current, 2N5205 Series

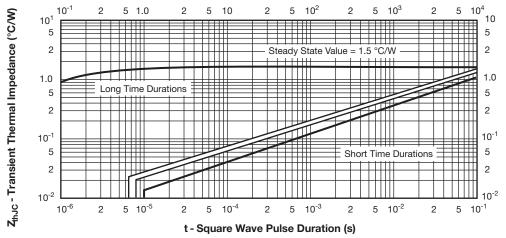


Fig. 15 - Maximum Transient Thermal Resistance, Junction to Case vs. Pulse Duration, 2N5205 Series

LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95333			



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for SCRs category:

Click to view products by Vishay manufacturer:

Other Similar products are found below:

NTE5428 T1500N16TOF VT T880N16TOF TT162N16KOF-A TT162N16KOF-K TT330N16AOF VS-22RIA20 VS-2N685 057219R

T1190N16TOF VT T1220N22TOF VT T201N70TOH T700N22TOF T830N18TOF TT250N12KOF-K VS-110RKI40 NTE5427 NTE5442

T2160N28TOF VT TT251N16KOF-K VS-22RIA100 VS-16RIA40 TD250N16KOF-A VS-ST110S16P0 T930N36TOF VT T2160N24TOF

VT T1190N18TOF VT T1590N28TOF VT 2N1776A T590N14TOF NTE5375 NTE5460 NTE5481 NTE5512 NTE5514 NTE5518

NTE5519 NTE5529 NTE5553 NTE5555 NTE5557 NTE5567 NTE5570 NTE5570 NTE5574 NTE5576 NTE5578 NTE5579 NTE5589

NTE5592